

L Number	Hits	Search Text	DB	Time stamp
1	67413	diode and (trench or groove or cavity or recess or void)	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/11/13 18:07
2	59423	((dopant or carrier or impurity) near concentration	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/11/13 18:08
3	3948	((diode and (trench or groove or cavity or recess or void)) and ((dopant or carrier or impurity) near concentration)) and	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/11/13 18:08
4	2030	((diode and (trench or groove or cavity or recess or void)) and ((dopant or carrier or impurity) near concentration)) and wafer	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/11/13 18:09